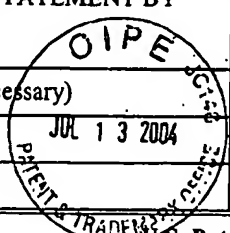


U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				SNDK.310US0		10/600,259	
				Applicant(s)			
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				06/20/03		Unknown	



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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
RL	001	6,529,410	3/2003	Han et al.			
	002	6,295,227	9/2001	Sakui et al.			
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RL	009	U.S. 2002/0093073	7/18/2002	Mori et al.			
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RL	011	International Search Report, PCT/US03/32119, filed 08/10/2003
	012	U.S. Patent Application No. 09/667,344, Yuan et al. 9/22/2000
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	014	Takeuchi, Y., et al., "A Self-Aligned STI Process Integration for Low Cost and Highly Reliable IGbit Flash Memories," 1998 Symposium on VLSI Technology; Digest of Technical Papers, IEEE, Honolulu, Hawaii, June 9-11, 1998, pp. 102-103.
✓	015	Lee, Jae-Duk, et al., "Effects of Parasitic Capacitance on NAND Flash Memory Cell Operation," Non-Volatile Semiconductor Memory Workshop, IEEE, Monterey, California, August 12-16, 2001, pp. 90-92.

Examiner	<i>U. K. K.</i>	Date Considered	8/25/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

U.S. Department of Commerce, Patent and Trademark		Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		SNDK.310US0		10/600,259	
		Applicant(s)			
(Use several sheets if necessary)		Jeffrey Lutze et al.			
		Filing Date		Group	
		06/20/03		Unknown	

U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

U.S. Published Patent Application Documents							
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	017	Chan, et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device," <i>IEEE Electron Device Letters</i> , Vol. EDL-8, No. 3, March 1987, pp. 93-95.
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